## **MSc Electronics**

## **ELH 401 - SOLID STATE ELECTRONICS**

Unit-I 15 Hours

Crystal properties and growth of semiconductors; semiconductor materials, crystal lattice, bulk crystal growth, epitaxial growth.

Atom and electrons; introduction to physical models, experimental observation, quantum mechanics, atomic structure and the periodic table.

Energy bands and charge carrier in semiconductors; bonding forces and energy bands in solids, charge carrier in semiconductors, carrier concentrations, drift of carrier in electric and magnetic fields, invariance of the Fermi level at equilibrium.

Unit-II 12 Hours

Excess carrier in semiconductors; optical absorption, luminescence, carrier life time and photo conductivity, diffusion of carriers,

Junctions; fabrication of pn-junction, equilibrium conditions, forward and reverse biased junctions: steady state conditions reverse biased breakdown, transient and AC conditions. Derivations from the simple theory, metal semiconductor junction, hetero junction.

Unit-III 15 Hours

Field effect transistor; transistor operation, the junction FET, the metal semiconductor FET, the metal insulator semiconductor FET, the MOS field effect transistor.

Bipolar junction transistor; fundamentals of BJT operations, amplifications with BJT, BJT fabrication, minority carrier distributions and terminal currents, generalized biasing, switching, other important effects, frequency limitations of transistors, hetero-junction BJT transistor.

## **Text Book**

1. "solid state electronic devices," B.G Streetman and S.K Banergee, PHI Pvt Ltd, 6<sup>th</sup>ed, 2006.

## **Reference:**

- 1. "Semiconductor Physics and Devices," D. A. Neamen, 4<sup>th</sup> Ed, McGraw-Hill, 2012
- 2. "Physics of Semiconductor Devices" S.M. Sze and Kwok K. Ng, 3<sup>rd</sup> Ed, Wily Interscience, 2007